

## 低消費電力の RS-485 ライン・ドライバとレシーバのペア

### 1 特長

- 長いケーブルを使用する高速マルチポイント・データ伝送用に設計
- 最小 30ns のパルス持続時間で動作
- 低消費電流: 5mA 以下
- ANSI 規格 RS-485 および ISO 8482:1987(E) の要件に適合またはそれを上回る性能
- パーティライン・バス用の 3 ステート出力
- 7V~12V の同相電圧範囲
- サーマル・シャットダウン保護機能により、バス競合によるドライバの損傷を防止
- 正および負の出力電流制限
- SN75ALS180 とピン互換

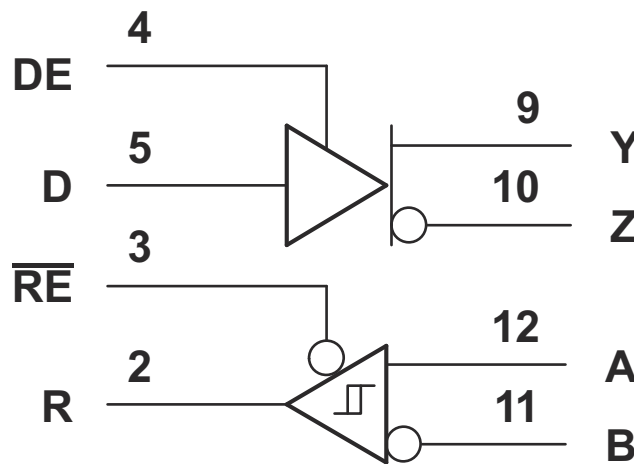
### 2 概要

SN55LBC180、SN65LBC180、SN75LBC180 差動ドライバとレシーバのペアは、伝送ラインの特性を考慮し、長いケーブルを使用する双方向データ通信向けに設計されたモノリシック IC です。これらのデバイスは、業界標準の ANSI RS-485 および ISO 8482:1987(E) の要件を満たすかそれを上回る、平衡型 (すなわち差動) 電圧モード・デバイスです。これらのデバイスは、テキサス・インスツルメンツ独自の LinBiCMOS™ を使用して設計されており、CMOS の低消費電力とバイポーラ・トランジスタの高精度および堅牢性を同じ回路内で実現します。

#### パッケージ情報

部品番号	パッケージ <sup>(1)</sup>	本体サイズ (公称)
SN75LBC180 SN65LBC180	N (PDIP)	19.3mm × 63.5mm
	D (SOIC)	8.65mm × 3.91mm
SN55LBC180	RSA (QFN)	4mm × 4mm
	RSA (QFN)	4mm × 4mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



論理図 (正論理)



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### 3 概要 (続き)

SN55LBC180、SN65LBC180、SN75LBC180 は、差動ライン・ドライバおよびレシーバと 3 ステート出力を組み合わせ、5V 単電源で動作します。ドライバとレシーバはそれぞれアクティブ HIGH、アクティブ LOW のイネーブルを備えており、それらのイネーブルを外部で接続することで、方向制御として機能させることができます。ドライバの差動出力とレシーバの差動入力、全二重動作のために個別の端子に接続されており、ディセーブルまたは電源オフ ( $V_{CC} = 0$ ) にかかわらず、バスに最小限の負荷を供給するように設計されています。これらのデバイスは同相電圧範囲が広いこと、ポイント・ツー・ポイントまたはマルチポイントのデータ・バス・アプリケーションに適しています。

またこれらのデバイスは、ライン・フォルト状態からの保護のために、正および負の出力電流制限機能とサーマル・シャットダウン機能を備えています。ライン・ドライバは、約 172°C の接合部温度でシャットダウンします。

SN75LBC180 は 0°C ~ 70°C の商用温度範囲で動作が規定されています。SN65LBC180 は -40°C ~ 85°C の産業用温度範囲で動作が規定されています。

SN55LBC180 は -55°C ~ 125°C の軍用温度範囲で動作が規定されています。

## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

### Changes from Revision H (June 2022) to Revision I (October 2022) Page

- Changed RSA (QFN) values in the *Thermal Information Table* .....6

### Changes from Revision G (April 2009) to Revision H (June 2022) Page

- 「注文情報」表を「パッケージ情報」表に変更 ..... 1
- Added the *Pin Configuration and Functions* ..... 4
- Added the *Thermal Information Table* ..... 6
- Fixed the typo in the unit for the Receiver enable  $I_{RH}$  to change the unit from A to  $\mu$ A..... 7
- Updated [図 6-1](#), [図 6-2](#), and [図 6-3](#), limiting the x-axis to a maximum of 70 mA driver output current..... 9
- Updated [図 9-1](#) to remove legacy terminology ..... 17

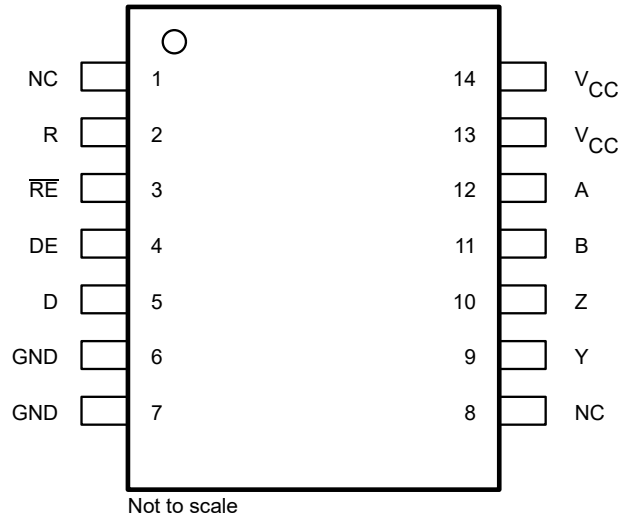
### Changes from Revision F (March 2009) to Revision G (April 2009) Page

- Added 3 ESD rows to the *Absolute Maximum Ratings* .....5

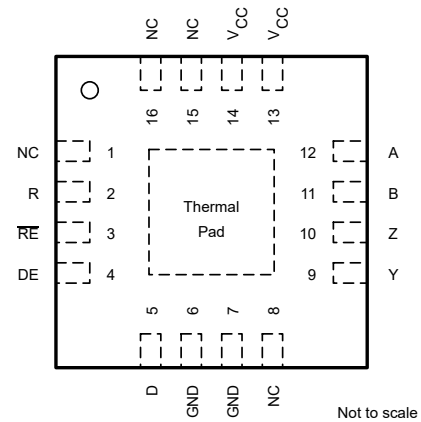
### Changes from Revision E (February 2006) to Revision F (March 2009) Page

- データシートのタイトルで「差動」を「RS-485」に変更..... 1
- デバイス番号 SN55LBC180 を追加。..... 1
- 「両方」を「これら」に変更 ..... 1
- 「注文情報」表を追加..... 1
- 「概要 (続き)」セクションを変更 ..... 2
- 「機能表」を変更し、先頭ページから「概要 (続き)」セクションに移動 ..... 2
- Deleted condition, moved cross reference..... 5
- Added all symbols in text that were not appearing in the PDF..... 5
- Deleted  $T_A$  row from the *Absolute Maximum Ratings* ..... 5
- Added the last column to *Dissipation Rating Table* ..... 5
- Added a row to  $T_A$  in the *Recommended Operating Conditions* for SN55LBC180..... 5
- Added SN55LB180 to the  $|V_{OD}|$  row..... 6
- Change: moved 5 max values to the min column (-1.5, -50, -100, -0.8, -0.8)..... 7
- Added the *Switching Characteristics: SN55LBC180* table ..... 8
- Changed moved schematics to the Typical Characteristics section..... 16

## 5 Pin Configuration and Functions



5-1. D OR N Package (SOIC)  
(Top View)



5-2. RSA Package (QFN)  
(Top View)

表 5-1. Pin Functions

PIN NAME	PIN NO		TYPE <sup>(1)</sup>	DESCRIPTION
	D Or N	RSA		
NC	1	1	NC	No internal connection
R	2	2	O	Receiver output
RE	3	3	I	Receiver enable input. Active low.
DE	4	4	I	Driver enable input. Active high
D	5	5	I	Driver input pin
GND	6, 7	6, 7	G	Ground connection. Pins 6 and 7 are connected together internally.
NC	8	8	NC	No internal connection
Y	9	9	O	Bus output port (complementary to Z)
Z	10	10	O	Bus output port (complementary to Y)
B	11	11	I	Bus input port (complementary to A)
A	12	12	I	Bus input port (complementary to B)
V <sub>CC</sub>	13, 14	13, 14	P	Supply input pins. Pins 13 and 14 are connected together internally.
NC	N/A	15, 16	NC	No internal connection

(1) Signal Types: I = Input, O = Output, P = Power input,

## 6 Specifications

### 6.1 Absolute Maximum Ratings

See note (1)

			UNIT	
V <sub>CC</sub>	Supply voltage range (2)	-0.3 to 7	V	
V <sub>BUS</sub>	Bus voltage range (A, B, Y, Z)(2)	-10 to 15	V	
	Voltage range at D, R, DE, $\overline{RE}$ (2)	-0.3 to V <sub>CC</sub> + 0.5	V	
	Continuous total power dissipation(3)	Internally limited		
	Total power dissipation	See Dissipation Rating Table		
T <sub>stg</sub>	Storage temperature range	-65 to 150	°C	
I <sub>O</sub>	Receiver output current range	-50 to 50	mA	
ESD	Electrostatic discharge	HBM (Human Body Model) EIA/JESD22-A114	±4	kV
		MM (Machine Model) EIA/JESD22-A115	400	V
		CDM (Charge Device Model) EIA/JESD22-C101	1.5	kV

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND.
- (3) The maximum operating junction temperature is internally limited. Use the dissipation rating table to operate below this temperature.

### 6.2 Dissipation Rating Table

PACKAGE(1)	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING	T <sub>A</sub> = 85°C POWER RATING	T <sub>A</sub> = 125°C POWER RATING
D	950 mW	7.6 mW/°C	608 mW	494 mW	—
N	1150 mW	9.2 mW/°C	736 mW	598 mW	—
RSA	3333 mW	26.67 mW/°C	2133 mW	1733 mW	400 mW

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at [www.ti.com](http://www.ti.com).

### 6.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT	
V <sub>CC</sub>	Supply voltage	4.75	5	5.25	V	
V <sub>IH</sub>	High-level input voltage	D, DE, and $\overline{RE}$		2	V	
V <sub>IL</sub>	Low-level input voltage	D, DE, and $\overline{RE}$		0.8	V	
V <sub>ID</sub>	Differential input voltage			-6(1)	6	V
V <sub>O</sub> , V <sub>I</sub> , or V <sub>IC</sub>	Voltage at any bus terminal (separately or common mode)	A, B, Y, or Z		-7(1)	12	V
I <sub>OH</sub>	High-level output current	Y or Z		-60	mA	
		R		-8		
I <sub>OL</sub>	Low-level output current	Y or Z		60	mA	
		R		8		
T <sub>A</sub>	Operating free-air temperature	SN55LBC180		-55	125	°C
		SN65LBC180		-40	85	
		SN75LBC180		0	70	

- (1) The algebraic convention where the least positive (more negative) limit is designated minimum, is used in this data sheet for the differential input voltage, voltage at any bus terminal, operating temperature, input threshold voltage, and common-mode output voltage.

## 6.4 Thermal Information Table

THERMAL METRIC <sup>(1)</sup>		D (SOIC)	N (PDIP)	RSA (QFN)	UNIT
		14 Pins	14 Pins	16 Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	93.2	53.4	38.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	47.5	40.0	35.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.4	33.2	17.5	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	11.2	19.0	1.1	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	48.9	32.9	17.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	7.9	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

## 6.5 Driver Section

### 6.5.1 Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP <sup>(1)</sup>	MAX	UNIT
$V_{IK}$	Input clamp voltage	$I_I = -18 \text{ mA}$				-1.5	V
$ V_{OD} $	Differential output voltage magnitude <sup>(2)</sup>	$R_L = 54 \Omega$ , See <a href="#">7-1</a>	SN55LBC180	1	2.5	5	V
			SN65LBC180	1.1	2.5	5	
			SN75LBC180	1.5	2.5	5	
		$R_L = 60 \Omega$ , See <a href="#">7-2</a>	SN55LBC180	1	2.5	5	
			SN65LBC180	1.1	2	5	
			SN75LBC180	1.5	2	5	
$\Delta V_{OD} $	Change in magnitude of differential output voltage <sup>(3)</sup>	See <a href="#">7-1</a> and <a href="#">7-2</a>				±0.2	V
$V_{OC}$	Common-mode output voltage			1	2.5	3	V
$\Delta V_{OC} $	Change in magnitude of common-mode output voltage <sup>(3)</sup>	$R_L = 54 \Omega$ ,	See <a href="#">7-1</a>			±0.2	V
$I_O$	Output current with power off	$V_{CC} = 0$ ,	$V_O = -7 \text{ V to } 12 \text{ V}$			±100	µA
$I_{OZ}$	High-impedance-state output current	$V_O = -7 \text{ V to } 12 \text{ V}$				±100	µA
$I_{IH}$	High-level input current	$V_I = 2.4 \text{ V}$				100	µA
$I_{IL}$	Low-level input current	$V_I = 0.4 \text{ V}$				100	µA
$I_{OS}$	Short-circuit output current	$-7 \text{ V} \leq V_O \leq 12 \text{ V}$				±250	mA
$I_{CC}$	Supply current	Receiver disabled	Outputs enabled			5	mA
			Outputs disabled			3	

(1) All typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25^\circ\text{C}$ .

(2) The minimum  $V_{OD}$  specification may not fully comply with ANSI RS-485 at operating temperatures below  $0^\circ\text{C}$ . System designers should take the possibly lower output signal into account in determining the maximum signal-transmission distance.

(3)  $\Delta|V_{OD}|$  and  $\Delta|V_{OC}|$  are the changes in the steady-state magnitude of  $V_{OD}$  and  $V_{OC}$ , respectively, that occur when the input is changed from a high level to a low level.

## 6.5.2 Switching Characteristics

$V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	$R_L = 54\ \Omega$ ,	See <a href="#">7-3</a>	7	12	18	ns
$t_{t(OD)}$	Differential output transition time			5	10	20	ns
$t_{PZH}$	Output enable time to high level	$R_L = 110\ \Omega$ ,	See <a href="#">7-4</a>			35	ns
$t_{PZL}$	Output enable time to low level	$R_L = 110\ \Omega$ ,	See <a href="#">7-5</a>			35	ns
$t_{PHZ}$	Output disable time from high level	$R_L = 110\ \Omega$ ,	See <a href="#">7-4</a>			50	ns
$t_{PLZ}$	Output disable time from low level	$R_L = 110\ \Omega$ ,	See <a href="#">7-5</a>			35	ns

## 6.5.3 Switching Characteristics: SN55LBC180

$V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$t_{d(OD)}$	Differential output delay time	$R_L = 54\ \Omega$ ,	See <a href="#">7-3</a>		15		ns
$t_{t(OD)}$	Differential output transition time				21		ns
$t_{PZH}$	Output enable time to high level	$R_L = 110\ \Omega$ ,	See <a href="#">7-4</a>		32		ns
$t_{PHZ}$	Output disable time from high level				55		
$t_{PZL}$	Output enable time to low level	$R_L = 110\ \Omega$ ,	See <a href="#">7-5</a>		32		ns
$t_{PLZ}$	Output disable time from low level				20		

## 6.6 Receiver Section

### 6.6.1 Electrical Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{IT+}$	Positive-going input threshold voltage	$I_O = -8\text{ mA}$				0.2	V
$V_{IT-}$	Negative-going input threshold voltage	$I_O = 8\text{ mA}$		-0.2			V
$V_{hys}$	Hysteresis voltage ( $V_{IT+} - V_{IT-}$ )				45		mV
$V_{IK}$	Enable-input clamp voltage	$I_I = -18\text{ mA}$		-1.5			V
$V_{OH}$	High-level output voltage	$V_{ID} = 200\text{ mV}$ ,	$I_{OH} = -8\text{ mA}$	3.5	4.5		V
$V_{OL}$	Low-level output voltage	$V_{ID} = -200\text{ mV}$ ,	$I_{OL} = 8\text{ mA}$		0.3	0.5	V
$I_{OZ}$	High-impedance-state output current	$V_O = 0\text{ V to }V_{CC}$				$\pm 20$	$\mu\text{A}$
$I_{IH}$	High-level enable-input current	$V_{IH} = 2.4\text{ V}$		-50			$\mu\text{A}$
$I_{IL}$	Low-level enable-input current	$V_{IL} = 0.4\text{ V}$		-100			$\mu\text{A}$
$I_I$	Bus input current	$V_I = 12\text{ V}$ , $V_{CC} = 5\text{ V}$ ,	Other input at 0 V		0.7	1	mA
		$V_I = 12\text{ V}$ , $V_{CC} = 0\text{ V}$ ,	Other input at 0 V		0.8	1	
		$V_I = -7\text{ V}$ , $V_{CC} = 5\text{ V}$ ,	Other input at 0 V	-0.8	-0.5		
		$V_I = -7\text{ V}$ , $V_{CC} = 0\text{ V}$ ,	Other input at 0 V	-0.8	-0.5		
$I_{CC}$	Supply current	Driver disabled	Outputs enabled			5	mA
			Outputs disabled			3	

### 6.6.2 Switching Characteristics

$V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PHL}$	Propagation delay time, high- to low-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V}$ , See <a href="#">7-6</a>	11	22	33	ns
$t_{PLH}$	Propagation delay time, low- to high-level output		11	22	33	ns
$t_{sk(p)}$	Pulse skew ( $ t_{PHL} - t_{PLH} $ )			3	6	ns
$t_t$	Transition time			5	8	ns
$t_{PZH}$	Output enable time to high level	See <a href="#">7-7</a>			35	ns
$t_{PZL}$	Output enable time to low level				30	ns
$t_{PHZ}$	Output disable time from high level				35	ns
$t_{PLZ}$	Output disable time from low level				30	ns

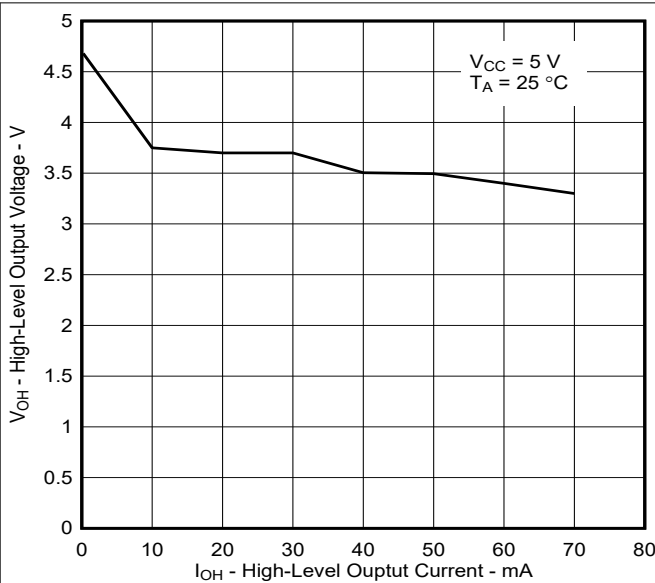
### 6.6.3 Switching Characteristics: SN55LBC180

$V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

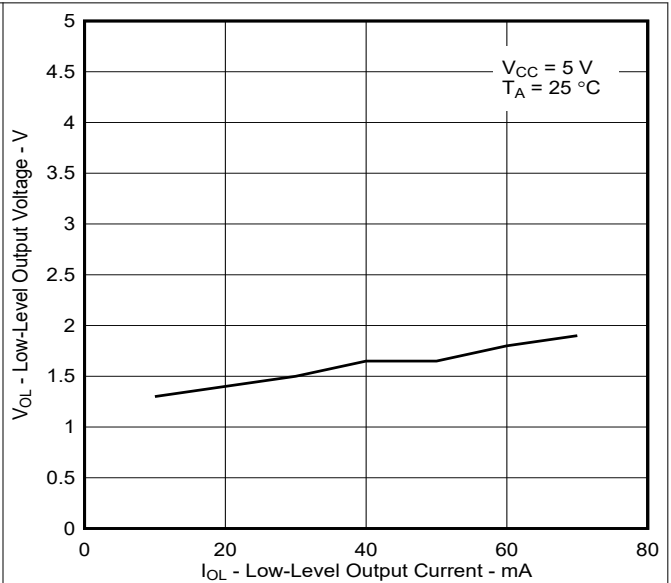
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PHL}$	Propagation delay time, high- to low-level output	$V_{ID} = -1.5\text{ V to }1.5\text{ V}$ , See <a href="#">7-6</a>		26		ns
$t_{PLH}$	Propagation delay time, low- to high-level output			23		ns
$t_{sk(p)}$	Pulse skew ( $ t_{PHL} - t_{PLH} $ )			3		ns
$t_{sk(p)t}$	Transition time			4		ns
$t_{PZH}$	Output enable time to high level	See <a href="#">7-4</a>		30		ns
$t_{PHZ}$	Output disable time from high level			26		ns
$t_{PZL}$	Output enable time to low level			30		ns
$t_{PLZ}$	Output disable time from low level			30		ns



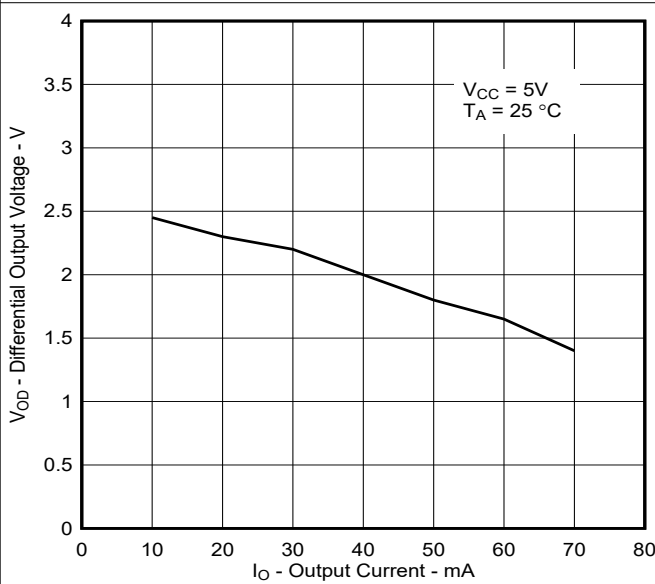
## 6.7 Typical Characteristics



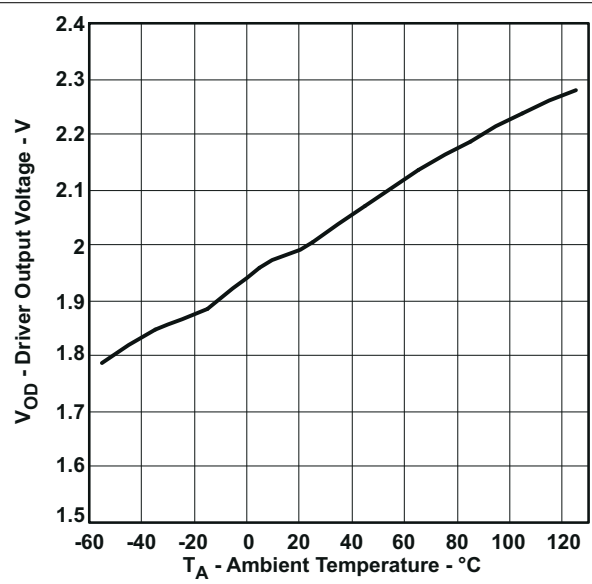
**6-1. Driver High-Level Output Voltage vs High-Level Output Current**



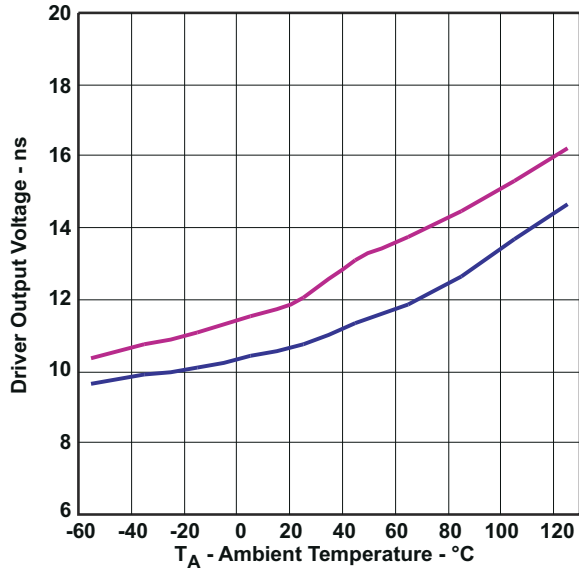
**6-2. Driver Low-Level Output Voltage vs Low-Level Output Current**



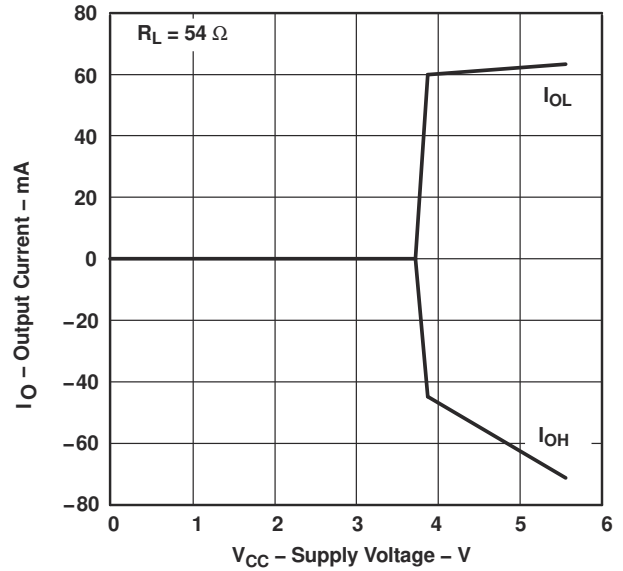
**6-3. Driver Differential Output Voltage vs Output Current**



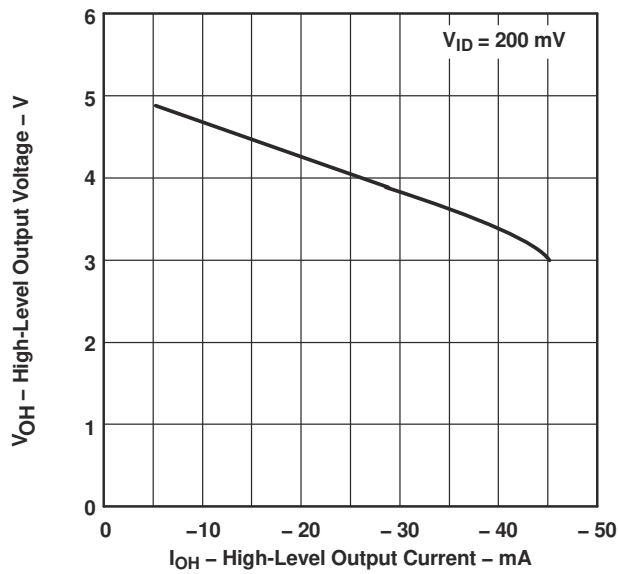
**6-4. Driver Differential Output Voltage vs Free-Air Temperature**



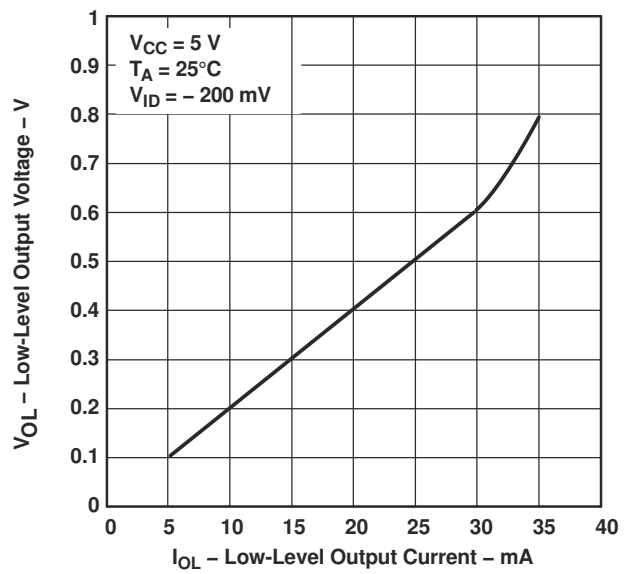
6-5. Driver Differential Delay Times vs Free-Air Temperature



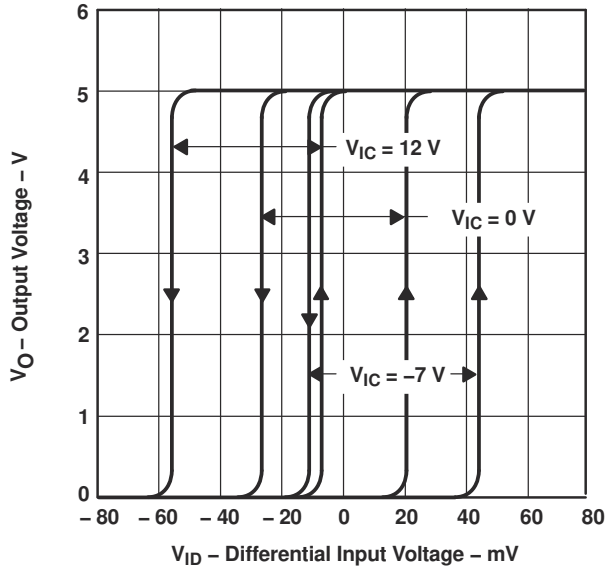
6-6. Driver Output Current vs Supply Voltage



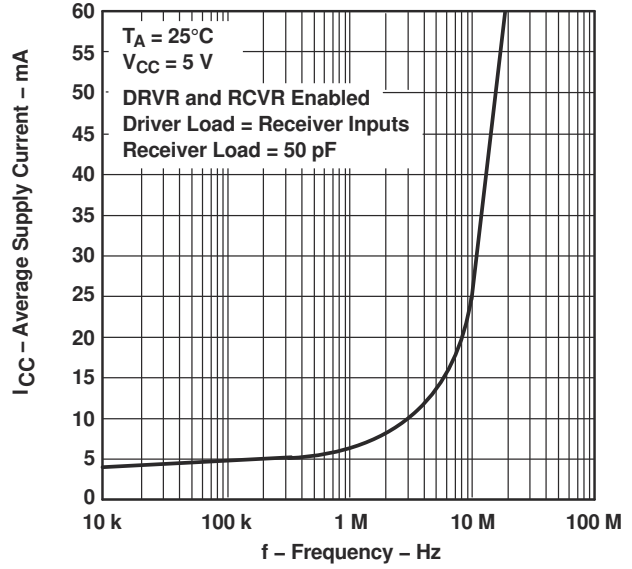
6-7. Receiver High-Level Output Voltage vs High-Level Output Current



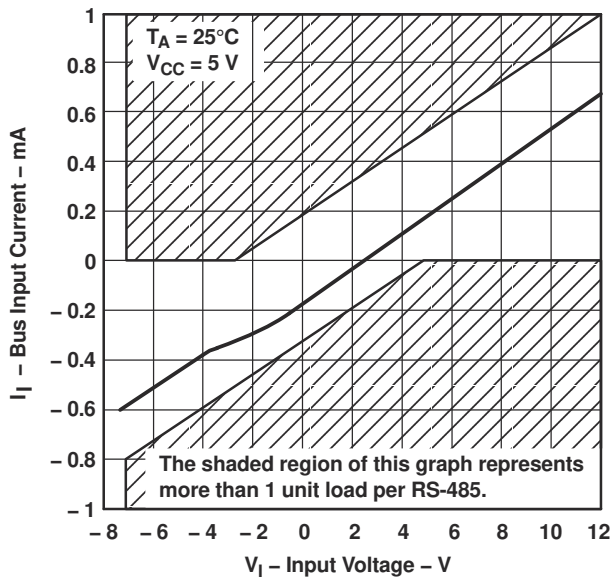
6-8. Receiver Low-Level Output Voltage vs Low-Level Output Current



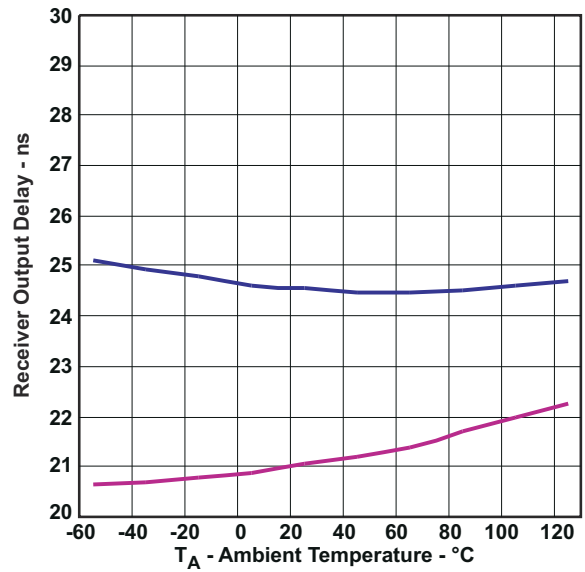
**6-9. Receiver Output Voltage vs Differential Input Voltage**



**6-10. Average Supply Current vs Frequency**

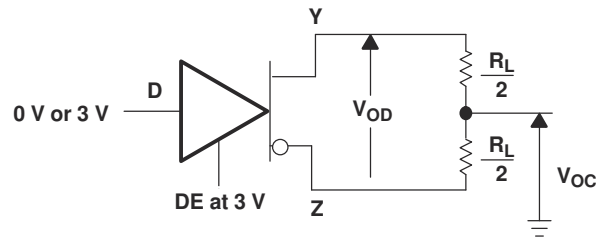


**6-11. Receiver Bus Input Current vs Input Voltage (Complementary Input at 0 V)**

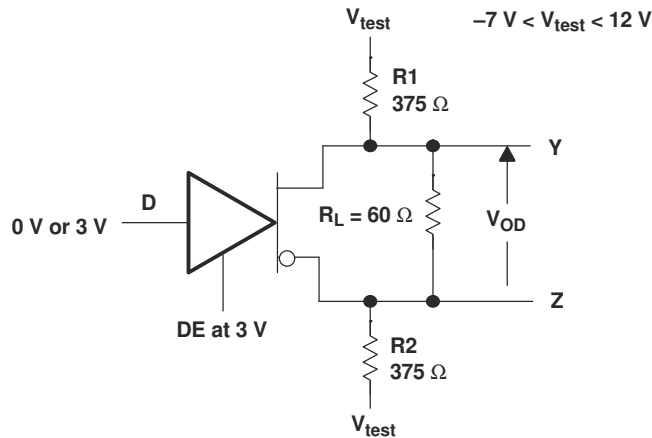


**6-12. Receiver Propagation DELAY T<sub>I</sub> vs Free-Air Temperature**

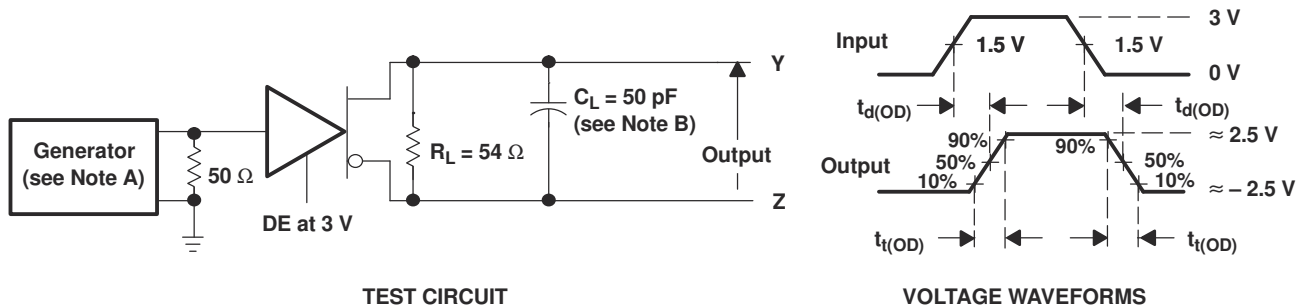
## 7 Parameter Measurement Information



7-1. Differential and Common-Mode Output Voltages

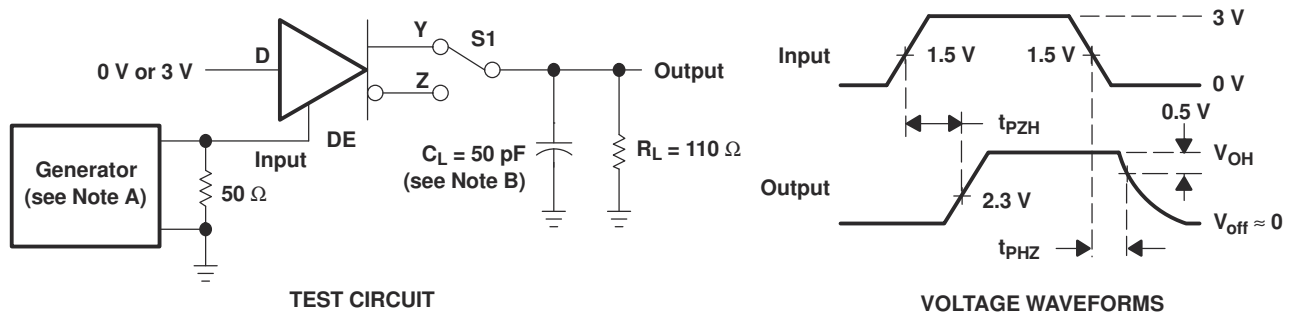


7-2. Driver  $V_{OD}$  Test Circuit

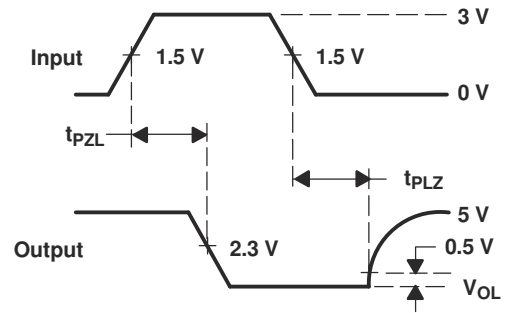
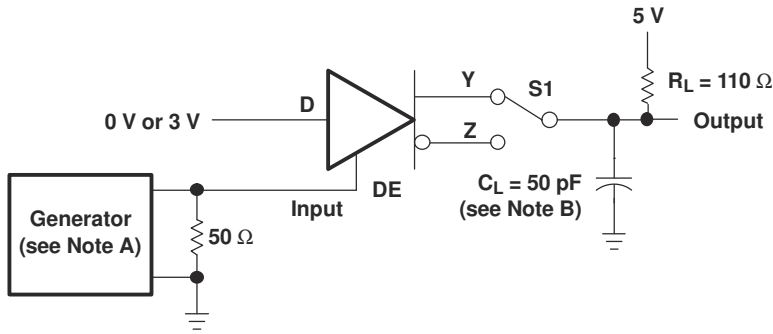


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR > 1 MHz, 50% duty cycle,  $t_r \leq 6$  ns,  $t_f \leq 6$  ns,  $Z_O = 50 \Omega$ .  
 B.  $C_L$  includes probe and jig capacitance.

7-3. Driver Test Circuit and Differential Output Delay and Transition Time Voltage Waveforms



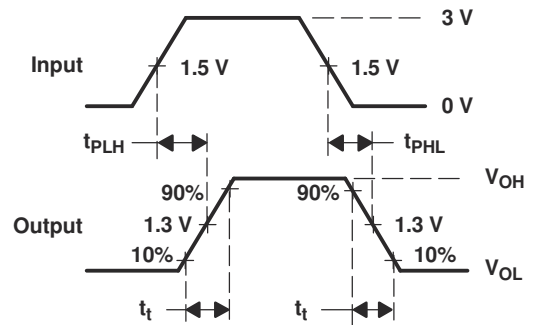
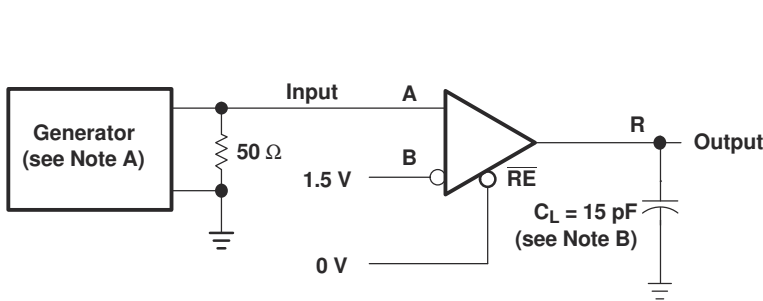
7-4. Driver Test Circuit and Enable and Disable Time Waveforms



TEST CIRCUIT

VOLTAGE WAVEFORMS

**7-5. Driver Test Circuit and Enable and Disable Time Voltage Waveforms**

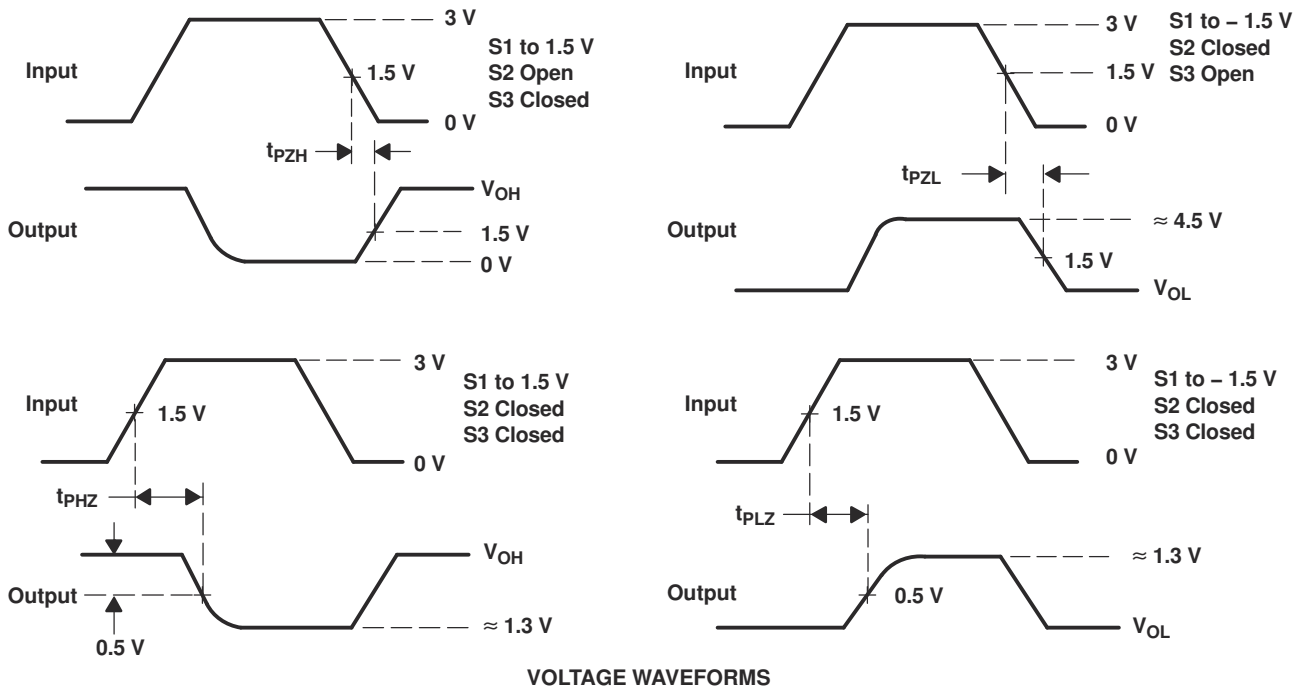
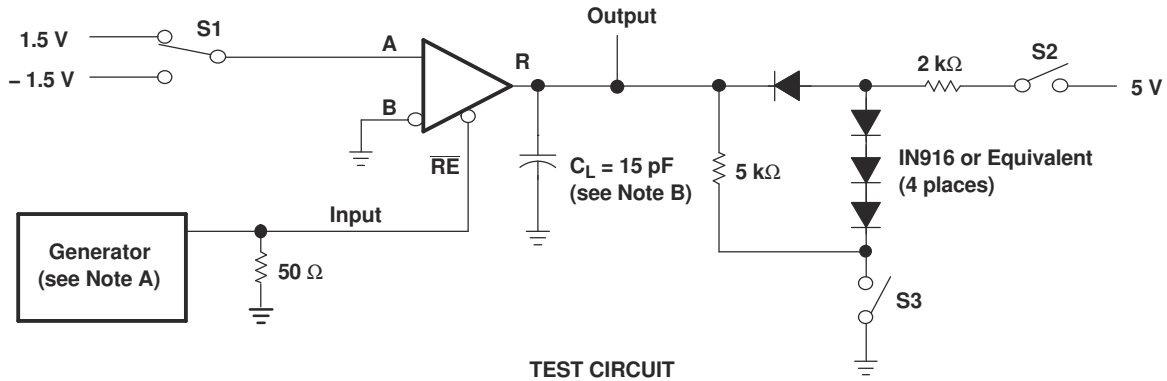


TEST CIRCUIT

VOLTAGE WAVEFORMS

- NOTES: A. The input pulse is supplied by a generator having the following characteristics:  $PRR \leq 1 \text{ MHz}$ , 50% duty cycle,  $t_r \leq 6 \text{ ns}$ ,  $t_f \leq 6 \text{ ns}$ ,  $Z_O = 50 \Omega$ .  
 B.  $C_L$  includes probe and jig capacitance.

**7-6. Receiver Test Circuit and Propagation Delay Time Voltage Waveforms**



- NOTES: A. The input pulse is supplied by a generator having the following characteristics:  $PRR \leq 1 \text{ MHz}$ , 50% duty cycle,  $t_r \leq 6 \text{ ns}$ ,  $t_f \leq 6 \text{ ns}$ ,  $Z_O = 50 \Omega$ .  
 B.  $C_L$  includes probe and jig capacitance.

**7-7. Receiver Output Enable and Disable Times**

## 8 Detailed Description

### 8.1 Function Tables

表 8-1. DRIVER

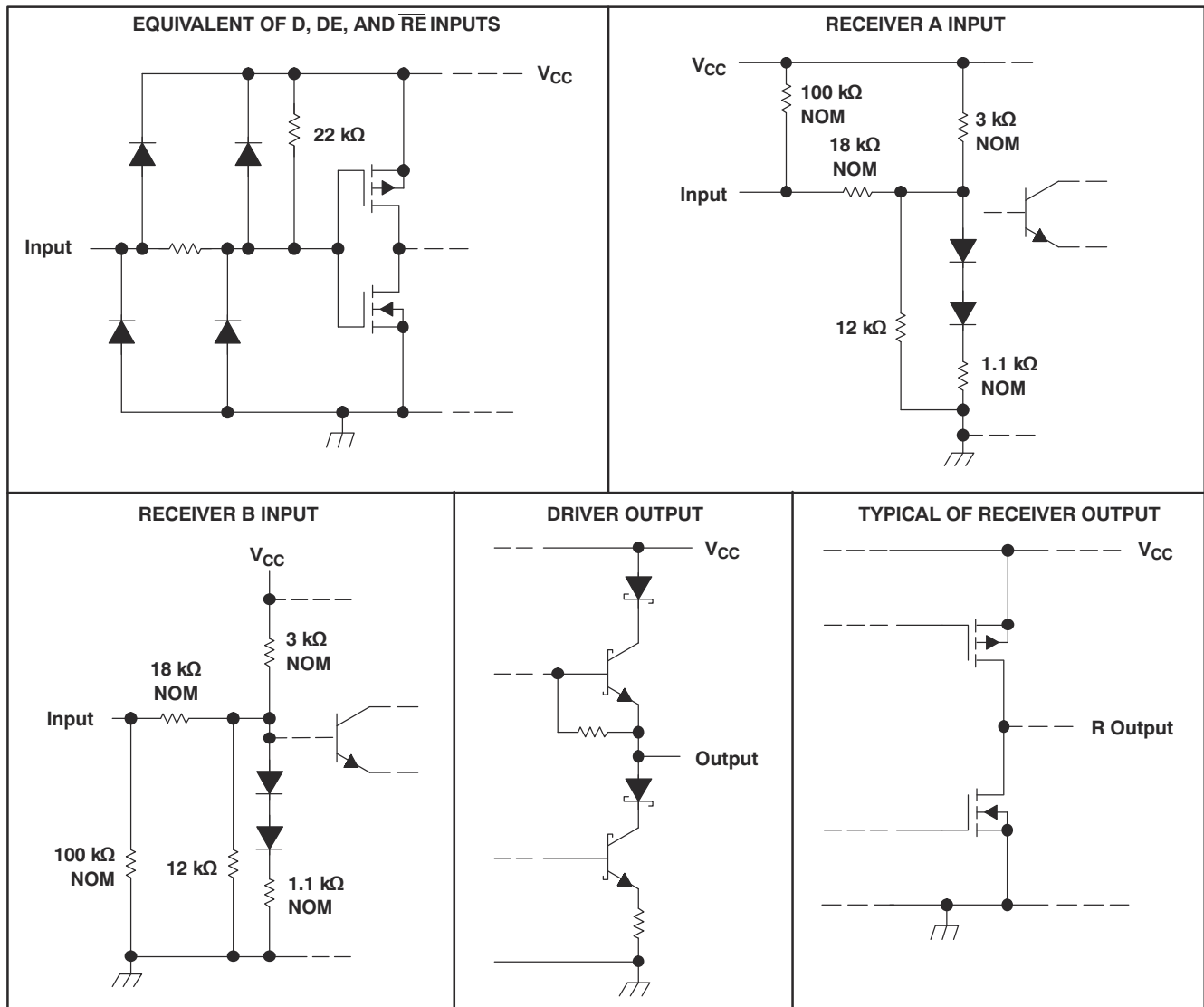
INPUT D <sup>(1)</sup>	ENABLE DE	OUTPUTS	
		Y	Z
H	H	H	L
L	H	L	H
X	L	Z	Z

(1) H = high level, L = low level, ? = Indeterminate, X = irrelevant,  
Z = high impedance (off)

表 8-2. RECEIVER

DIFFERENTIAL INPUTS A-B	ENABLE RE	OUTPUT R	
		Y	Z
$V_{ID} \geq 0.2\text{ V}$	L	H	
$-0.2\text{ V} < V_{ID} < 0.2\text{ V}$	L	?	
$V_{ID} \leq -0.2\text{ V}$	L	L	
X	H	Z	
Open circuit	L	H	

## 8.2 Schematics of Inputs and Outputs





## 9 Application and Implementation

### 注

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### 9.1 Application Information

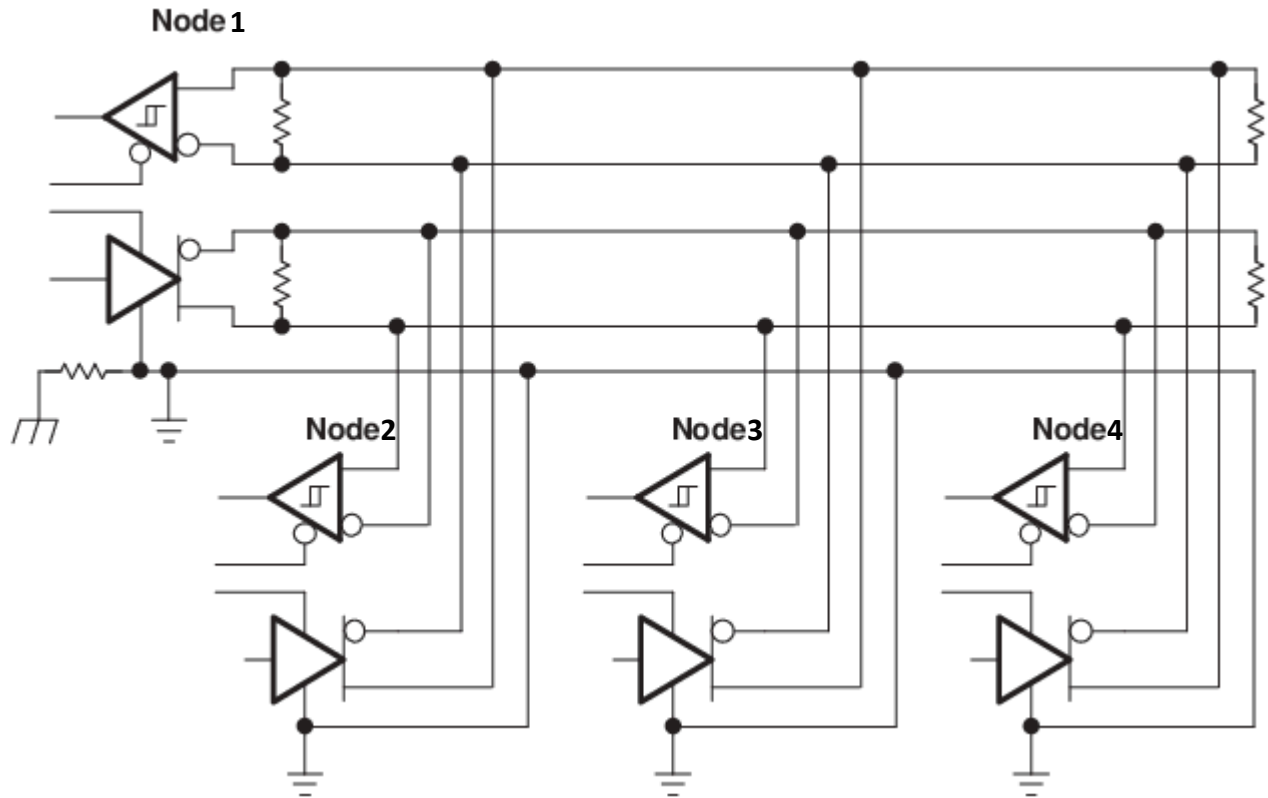


図 9-1. Full Duplex Application Circuit

## 10 Device and Documentation Support

### 10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.2 サポート・リソース

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TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

### 10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN55LBC180RSAR	ACTIVE	QFN	RSA	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	SN55 LBC180	<a href="#">Samples</a>
SN65LBC180DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB180	<a href="#">Samples</a>
SN65LBC180DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	6LB180	<a href="#">Samples</a>
SN65LBC180N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN65LBC180N	<a href="#">Samples</a>
SN65LBC180RSAR	ACTIVE	QFN	RSA	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BL180	<a href="#">Samples</a>
SN75LBC180N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75LBC180N	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF SN55LBC180, SN75LBC180 :**

- Catalog : [SN75LBC180](#)
- Military : [SN55LBC180](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

## TAPE AND REEL INFORMATION



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN55LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
SN65LBC180DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN65LBC180RSAR	QFN	RSA	16	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN55LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0
SN65LBC180DR	SOIC	D	14	2500	356.0	356.0	35.0
SN65LBC180RSAR	QFN	RSA	16	3000	367.0	367.0	35.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65LBC180N	N	PDIP	14	25	506	13.97	11230	4.32
SN75LBC180N	N	PDIP	14	25	506	13.97	11230	4.32

N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - $\triangle C$  Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - $\triangle D$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



## GENERIC PACKAGE VIEW

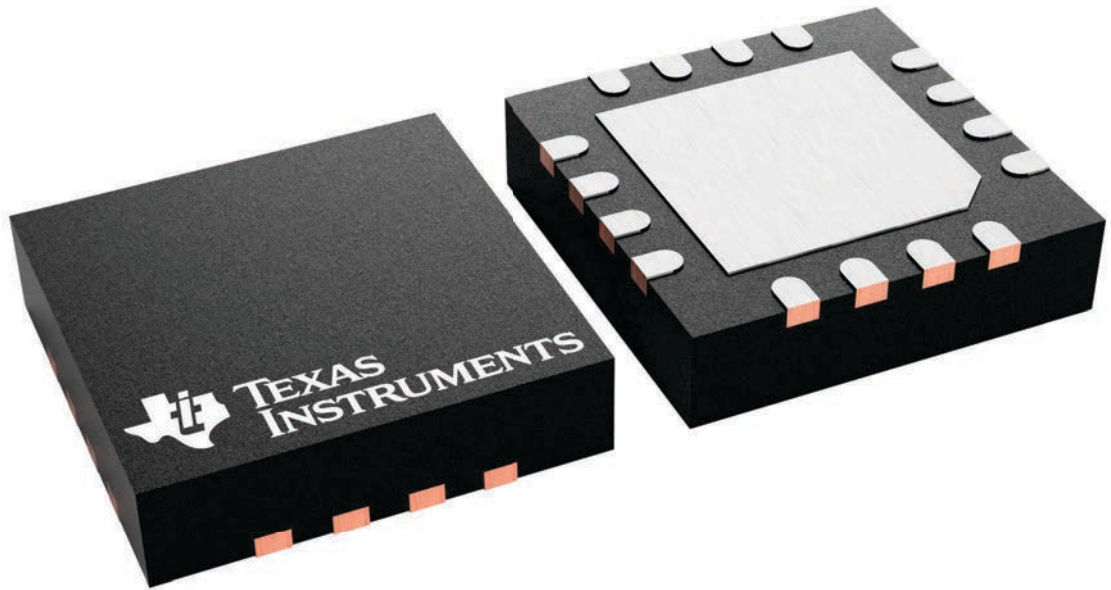
**RSA 16**

**VQFN - 1 mm max height**

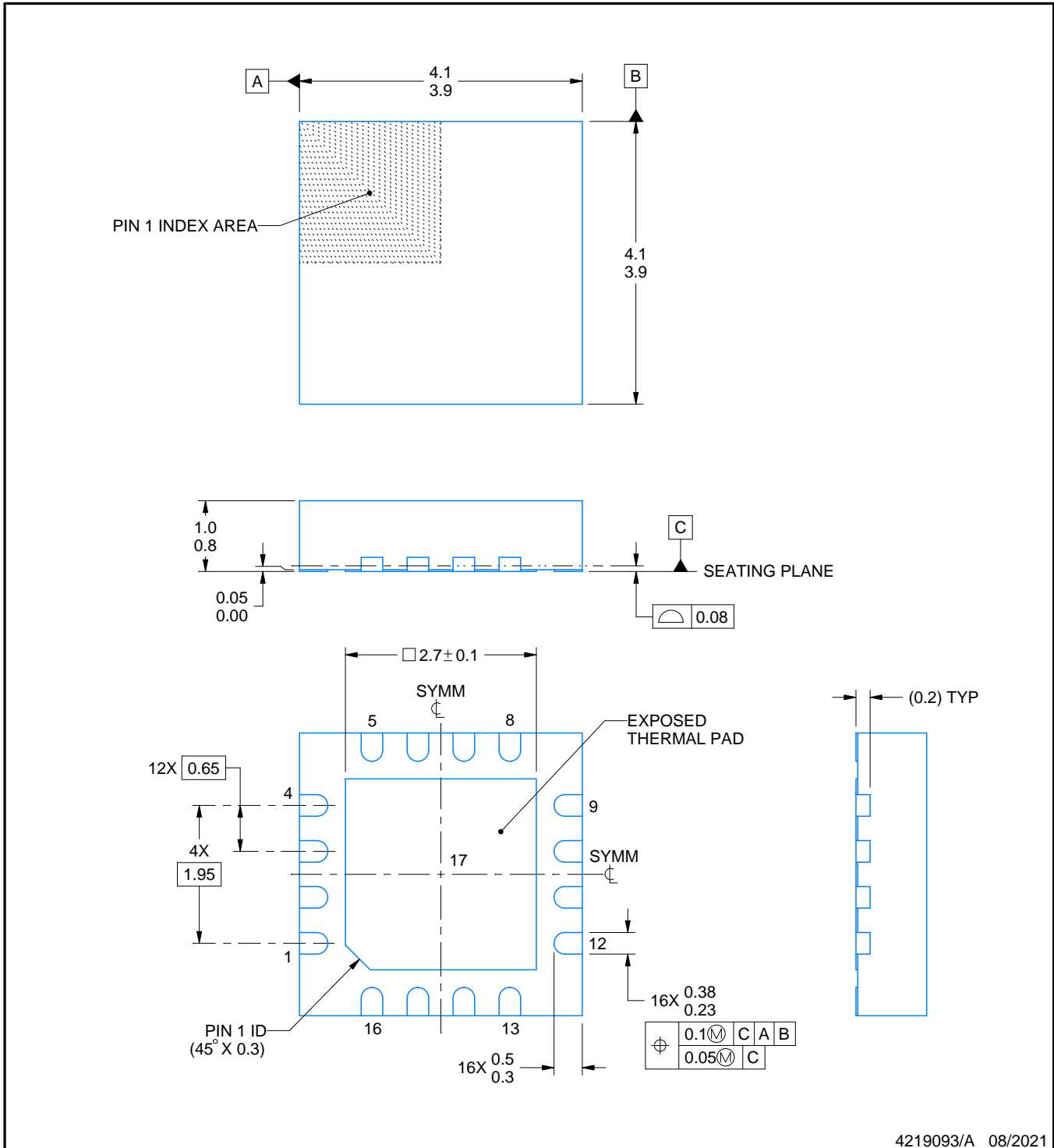
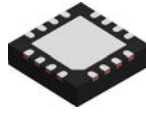
4 x 4, 0.65 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4230969/A



4219093/A 08/2021

NOTES:

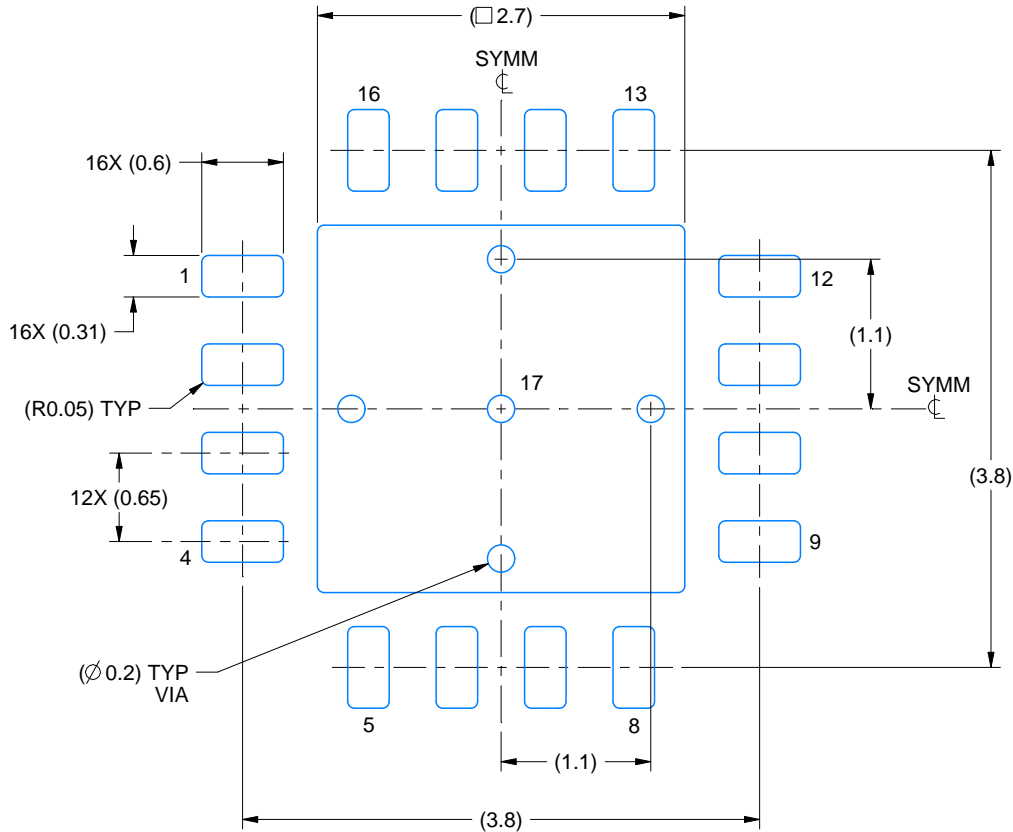
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.
4. Reference JEDEC registration MO-220.

# EXAMPLE BOARD LAYOUT

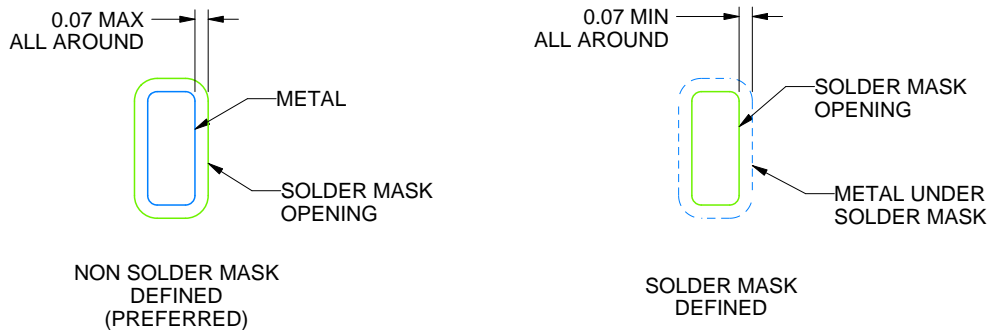
RSA0016B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:18X



SOLDER MASK DETAILS

4219093/A 08/2021

NOTES: (continued)

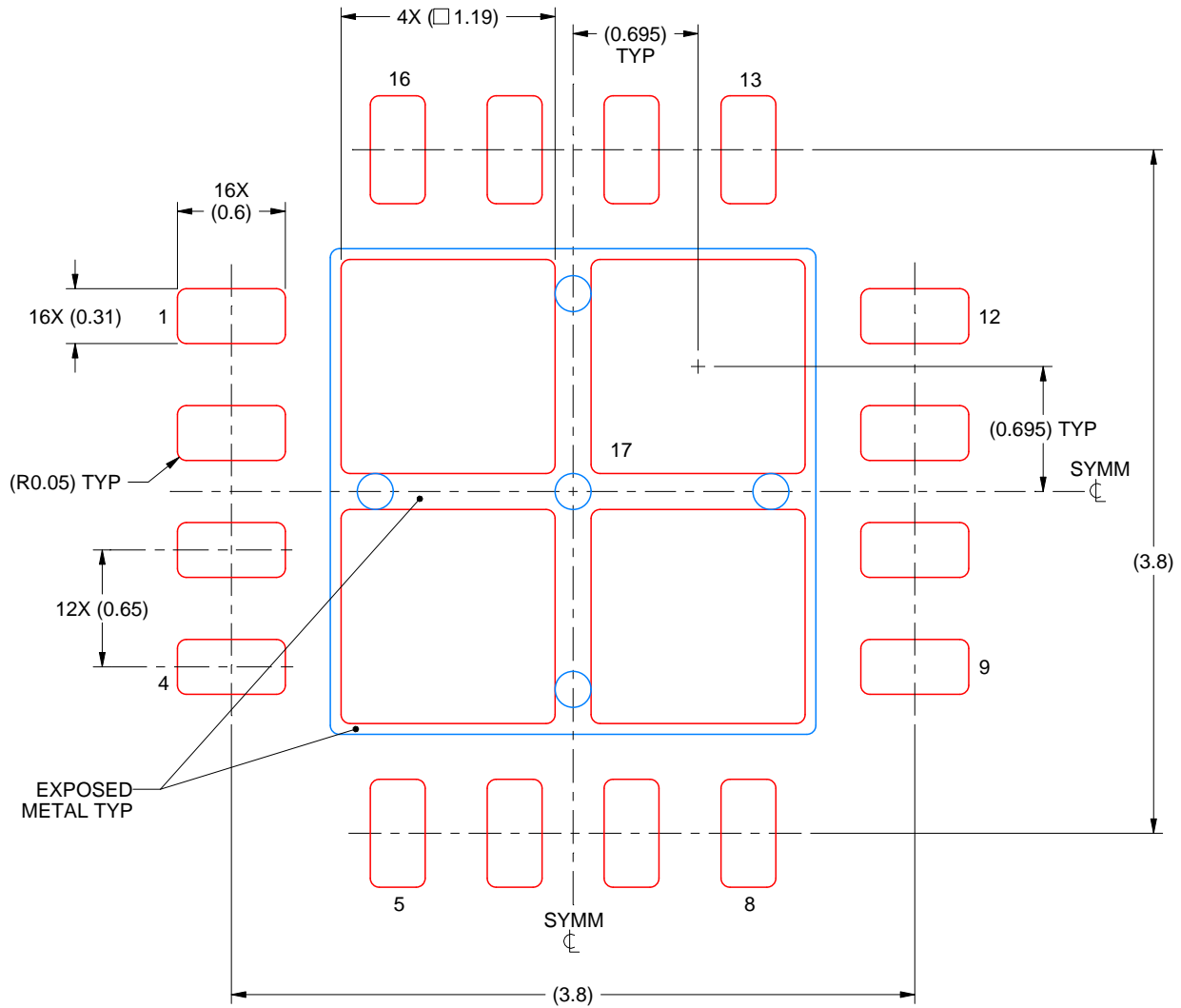
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

RSA0016B

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD  
77% PRINTED SOLDER COVERAGE BY AREA  
SCALE:25X

4219093/A 08/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  -  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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